

# **isc Silicon NPN Darlington Power Transistor**

2SD971

#### **DESCRIPTION**

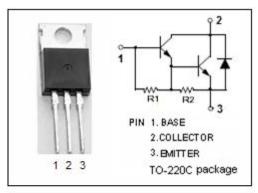
- · High Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO} = 300V(Min)$
- · High DC Current Gain
- · High Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

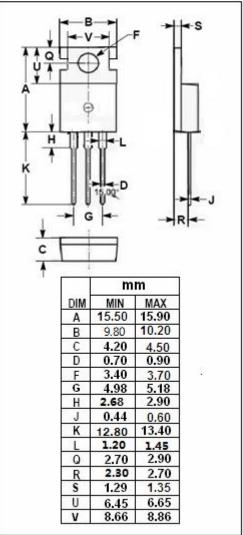


 Designed for applications such as electronic ignition, DC and AC motor controls, solenoid drivers, etc.

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	300	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	300	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	٧	
lc	Collector Current-Continuous	6	А	
I <sub>CP</sub>	Collector Current-Peak	10	Α	
I <sub>B</sub>	Base Current	1	Α	
Pc	Collector Power Dissipation $@T_C=25^{\circ}C$	50	W	
Tj	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
VCEO(SUS)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ;I <sub>B</sub> = 0	300			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 50mA			1.8	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> =100mA			1.8	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 50mA			2.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 100mA			2.5	V
Ices	Collector Cutoff Current	V <sub>CE</sub> = 300V; V <sub>BE</sub> = 0 V <sub>CE</sub> = 300V; V <sub>BE</sub> = 0,T <sub>C</sub> = 125°C			1 5	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 300V; I <sub>B</sub> = 0			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	mA
h <sub>FE</sub>	DC Current Gain	Ic= 2A; V <sub>CE</sub> = 2V	2000			
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 4A			2.5	V

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